

Walter Meyer

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6024697/publications.pdf>

Version: 2024-02-01

111
papers

1,367
citations

430874
18
h-index

395702
33
g-index

111
all docs

111
docs citations

111
times ranked

1166
citing authors

#	ARTICLE	IF	CITATIONS
1	DLTS study of the influence of annealing on deep level defects induced in xenon ions implanted n-type 4H-SiC. Journal of Materials Science: Materials in Electronics, 2022, 33, 15679-15688.	2.2	2
2	Effect of Isovalent Doping on Hydrogen Passivated Vacancy-oxygen Defect Complexes in Silicon: Insights from Density Functional Theory. Silicon, 2021, 13, 1969-1977.	3.3	2
3	Deep-level transient spectroscopy of GaN grown by electrochemical deposition and irradiated with alpha particles. Materials Science in Semiconductor Processing, 2021, 127, 105685.	4.0	3
4	First-principles Study of the Impact of Hydrogen Passivation on the Charge State Transition Levels of the $\text{CiOi}(\text{Sii})_n$ Defect Complexes in Silicon. Silicon, 2020, 12, 2699-2704.	3.3	1
5	Effect of electron radiation on small-signal parameters of NMOS devices at mm-wave frequencies. Microelectronics Reliability, 2020, 107, 113598.	1.7	2
6	Ti- and Fe-related charge transition levels in $\text{In}^{2+}\text{Ga}_2\text{O}_3$. Applied Physics Letters, 2020, 116, .	3.3	37
7	Determination of capture barrier energy of the E-center in palladium Schottky barrier diodes of antimony-doped germanium by varying the pulse width. Materials Research Express, 2020, , .	1.6	2
8	Ab initio study of the effect of hydrogen passivation on boron-oxygen-carbon related defect complexes in silicon. Materials Science in Semiconductor Processing, 2020, 110, 104967.	4.0	3
9	Electrical characterization of electron beam exposure induced defects in epitaxially grown n-type silicon. AIP Conference Proceedings, 2019, , .	0.4	1
10	Effects of thermal treatment on structural, optical and electrical properties of NiO thin films. Physica B: Condensed Matter, 2019, 575, 411694.	2.7	15
11	Influence (Ce and Sm) co-doping ZnO nanorods on the structural, optical and electrical properties of the fabricated Schottky diode using chemical bath deposition. Journal of Alloys and Compounds, 2019, 810, 151929.	5.5	18
12	Electronic properties and defect levels induced by group III substitutional interstitial complexes in Ge. Journal of Materials Science, 2019, 54, 10798-10808.	3.7	4
13	The influence of thermal annealing on the characteristics of Au/Ni Schottky contacts on n-type 4H-SiC. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	2.3	6
14	Electrically active induced energy levels and metastability of B and N vacancy-complexes in 4H-SiC. Journal of Physics Condensed Matter, 2018, 30, 185702.	1.8	4
15	Structural, optical and electrical characteristics of nickel oxide thin films synthesised through chemical processing method. Physica B: Condensed Matter, 2018, 535, 24-28.	2.7	15
16	Electrically active defects in p-type silicon after alpha-particle irradiation. Physica B: Condensed Matter, 2018, 535, 99-101.	2.7	3
17	Laplace DLTS study of the fine structure and metastability of the radiation-induced E3 defect level in GaAs. Semiconductor Science and Technology, 2018, 33, 125011.	2.0	2
18	7. Metastability of the boron-vacancy complex in silicon: Insights from hybrid functional calculations. , 2018, , 113-122.		0

#	ARTICLE	IF	CITATIONS
19	Metastability of the boron-vacancy complex in silicon: Insights from hybrid functional calculations. Physical Sciences Reviews, 2018, 3, .	0.8	0
20	Properties of a previously unobserved donor-related electrically active defect in Ge induced by alpha particle irradiation. Nuclear Instruments & Methods in Physics Research B, 2017, 406, 680-682.	1.4	1
21	Ab-initio Study of Aluminium Impurity and Interstitial-Substitutional Complexes in Ge Using a Hybrid Functional (HSE). Journal of Electronic Materials, 2017, 46, 3880-3887.	2.2	7
22	Rare Earth Interstitials in Ge: A Hybrid Density Functional Theory Study. Journal of Electronic Materials, 2017, 46, 1022-1029.	2.2	8
23	Electrical Characterization of High Energy Electron Irradiated Ni/4H-SiC Schottky Barrier Diodes. Journal of Electronic Materials, 2016, 45, 4177-4182.	2.2	13
24	The carbon-substitutional-carbon-interstitial (CsCi) defect pair in silicon from hybrid functional calculations. Computational Materials Science, 2016, 118, 338-341.	3.0	6
25	Electrical characterization of deep levels created by bombarding nitrogen-doped 4H-SiC with alpha-particle irradiation. Nuclear Instruments & Methods in Physics Research B, 2016, 371, 312-316.	1.4	23
26	Electrical Characterization of Defects Introduced in n -Type N-Doped 4H-SiC during Electron Beam Exposure. Solid State Phenomena, 2015, 242, 427-433.	0.3	3
27	Determination of the mean and the homogeneous barrier height of Cu Schottky contacts on heteroepitaxial $\text{InGa}_{2/3}\text{O}_{3/3}$ thin films grown by pulsed laser deposition. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 40-47.	1.8	111
28	Observation of low-temperature annealing of a primary defect in gallium nitride. Physica B: Condensed Matter, 2014, 439, 64-66.	2.7	1
29	Ab initio study of metastability of Eu^{3+} defect complexes in GaN. Physica B: Condensed Matter, 2014, 439, 141-143.	2.7	6
30	Introduction and annealing of primary defects in proton-bombarded n -GaN. Physica Status Solidi (B): Basic Research, 2014, 251, 211-218.	1.5	5
31	A study of the T2 defect and the emission properties of the E3 deep level in annealed melt grown ZnO single crystals. Journal of Applied Physics, 2013, 113, 124502.	2.5	9
32	Field dependence of the $E1^{\text{e}2}$ and $M3^{\text{e}2}$ electron traps in inductively coupled Ar plasma treated n-Gallium Arsenide. Journal of Applied Physics, 2012, 111, 093703.	2.5	1
33	Effects of high temperature annealing on single crystal ZnO and ZnO devices. Journal of Applied Physics, 2012, 111, .	2.5	15
34	Effects of hydrogen, oxygen, and argon annealing on the electrical properties of ZnO and ZnO devices studied by current-voltage, deep level transient spectroscopy, and Laplace DLTS. Journal of Applied Physics, 2012, 111, 094504.	2.5	29
35	Electrical characterization of defects introduced in n -Si during electron beam deposition of Pt. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 1926-1933.	1.8	9
36	Ar plasma induced deep levels in epitaxial n-GaAs. Journal of Applied Physics, 2012, 111, 013703.	2.5	5

#	ARTICLE	IF	CITATIONS
37	Inductively coupled plasma induced deep levels in epitaxial n-GaAs. Physica B: Condensed Matter, 2012, 407, 1497-1500.	2.7	5
38	Characterization of AlGaIn-based metal-semiconductor solar-blind UV photodiodes with IrO ₂ Schottky contacts. Physica B: Condensed Matter, 2012, 407, 1529-1532.	2.7	6
39	Interface properties of an O ₂ annealed Au/Ni/n-Al _{0.18} Ga _{0.82} N Schottky contact. Physica B: Condensed Matter, 2012, 407, 1599-1602.	2.7	0
40	Optoelectronic characterization of Au/Ni/n-AlGaIn photodiodes after annealing at different temperatures. Physica B: Condensed Matter, 2012, 407, 1628-1630.	2.7	4
41	Comparison of two models for phonon assisted tunneling field enhanced emission from defects in Ge measured by DLTS. Physica B: Condensed Matter, 2012, 407, 1641-1644.	2.7	1
42	A comparative study of the electrical properties of Pd/ZnO Schottky contacts fabricated using electron beam deposition and resistive/thermal evaporation techniques. Journal of Applied Physics, 2011, 110, 094504.	2.5	13
43	Defect introduction in Ge during inductively coupled plasma etching and Schottky barrier diode fabrication processes. Thin Solid Films, 2010, 518, 2485-2488.	1.8	8
44	The dependence of barrier height on temperature for Pd Schottky contacts on ZnO. Physica B: Condensed Matter, 2009, 404, 4402-4405.	2.7	34
45	Current-temperature measurements of a SBD evaporated onto inductively coupled plasma cleaned germanium. Physica B: Condensed Matter, 2009, 404, 4389-4392.	2.7	0
46	Electronic and annealing properties of the E0.31 defect introduced during Ar plasma etching of germanium. Physica B: Condensed Matter, 2009, 404, 4376-4378.	2.7	8
47	Electrical characterization of defects introduced in Ge during electron beam deposition of different metals. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 159-161.	1.8	11
48	Electrical characterization of defects introduced during metallization processes in n-type germanium. Materials Science in Semiconductor Processing, 2008, 11, 348-353.	4.0	4
49	Electronic properties of shallow level defects in ZnO grown by pulsed laser deposition. Journal of Physics: Conference Series, 2008, 100, 042038.	0.4	4
50	Dependence of Trap Concentrations in ZnO Thin Films on Annealing Conditions. Journal of the Korean Physical Society, 2008, 53, 2861-2863.	0.7	17
51	Electrical characterization of defects in heavy-ion implanted n-type Ge. Nuclear Instruments & Methods in Physics Research B, 2007, 257, 169-171.	1.4	9
52	Electronic properties of defects in pulsed-laser deposition grown ZnO with levels at 300 and 370meV below the conduction band. Physica B: Condensed Matter, 2007, 401-402, 378-381.	2.7	30
53	Electrical Characterization of Defects Introduced During Sputter Deposition of Schottky Contacts on n-type Ge. Journal of Electronic Materials, 2007, 36, 1604-1607.	2.2	9
54	Electrical characterization of defects introduced during electron beam deposition of Schottky contacts on n-type Ge. Materials Science in Semiconductor Processing, 2006, 9, 576-579.	4.0	10

#	ARTICLE	IF	CITATIONS
55	Electrical Characterization of Proton Irradiated n-Type ZnO. Materials Research Society Symposia Proceedings, 2006, 957, 1.	0.1	0
56	Electrical characterization of defects introduced during electron beam deposition of Pd Schottky contacts on n-type Ge. Applied Physics Letters, 2006, 88, 242110.	3.3	38
57	Electrical characterization of defects introduced in n-type Ge during indium implantation. Applied Physics Letters, 2006, 89, 152123.	3.3	15
58	Reactivation and passivation of the $E_c - 0.61$ eV deep level in GaN. Physica Status Solidi A, 2004, 201, 2277-2280.	1.7	2
59	Electrical characterisation of hole traps in n-type GaN. Physica Status Solidi A, 2004, 201, 2271-2276.	1.7	29
60	Electrical characterisation of NiO/ZnO structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 674-677.	0.8	15
61	Effect of thermal radiation on electron emission from the E2 defect in n-GaAs. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2333-2336.	0.8	0
62	Fabrication and characterisation of NiO/ZnO structures. Sensors and Actuators B: Chemical, 2004, 100, 270-276.	7.8	57
63	Electrical characterization of as-grown and particle irradiated n-type bulk ZnO. , 2004, , .		0
64	Bias-dependent deep level in HVPE n-GaN. Physica B: Condensed Matter, 2003, 340-342, 475-478.	2.7	9
65	Electrical defects introduced during high-temperature irradiation of GaN and AlGaIn. Physica B: Condensed Matter, 2003, 340-342, 421-425.	2.7	23
66	Electron emission properties of a defect at $\sim \frac{1}{4}(E_c + 0.23\text{eV})$ in impurity-free disordered n-GaAs. Physica B: Condensed Matter, 2003, 340-342, 315-319.	2.7	1
67	Defect Engineering and Atomic Relocation Processes in Impurity-Free Disordered GaAs and AlGaAs. Materials Research Society Symposia Proceedings, 2003, 799, 1.	0.1	0
68	Electrical characterization of vapor-phase-grown single-crystal ZnO. Applied Physics Letters, 2002, 80, 1340-1342.	3.3	171
69	Electron traps created in n-type GaN during 25 keV hydrogen implantation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 6-9.	3.5	3
70	Defects Created by 25 keV Hydrogen Implantation in n-type GaN. Materials Research Society Symposia Proceedings, 2001, 693, 44.	0.1	0
71	Electrical characterization of growth-induced defects in n-GaN. Radiation Effects and Defects in Solids, 2001, 156, 255-259.	1.2	4
72	Metallisation induced electron traps in epitaxially grown n-type GaN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 71, 77-81.	3.5	10

#	ARTICLE	IF	CITATIONS
73	Configurational metastable defects in irradiated epitaxially grown boron-doped p-type Si. Physical Review B, 2000, 63, .	3.2	13
74	Metastable-like behaviour of a sputter deposition-induced electron trap in n-GaN. Physica B: Condensed Matter, 1999, 273-274, 92-95.	2.7	18
75	Emission kinetics of electron traps introduced in n-GaN during He-ion irradiation. Nuclear Instruments & Methods in Physics Research B, 1999, 148, 474-477.	1.4	7
76	The influence of high-energy alpha-particle irradiation on the spectral and defect properties of a Si photovoltaic detector. Semiconductor Science and Technology, 1999, 14, 323-326.	2.0	7
77	Electric-field-enhanced emission and annealing behaviour of electron traps introduced in n-Si by low-energy He ion bombardment. Semiconductor Science and Technology, 1999, 14, 41-47.	2.0	35
78	Summary of Schottky barrier height data on epitaxially grown n- and p-GaAs. Thin Solid Films, 1998, 325, 181-186.	1.8	40
79	Electronic and transformation properties of a metastable defect introduced in epitaxially grown boron-doped p-type Si by alpha particle irradiation. Applied Physics Letters, 1998, 72, 3178-3180.	3.3	9
80	A deep level transient spectroscopy characterization of defects induced in epitaxially grown n-Si by low-energy He-ion bombardment. Journal of Applied Physics, 1998, 83, 5576-5578.	2.5	16
81	Electrical characterization of He-plasma processed n-GaAs. Journal of Applied Physics, 1998, 84, 1973-1976.	2.5	7
82	Fermi level pinning by metal Schottky contacts on n type GaAs. Materials Science and Technology, 1998, 14, 1269-1272.	1.6	3
83	Characterization of a Metastable Defect Introduced In Epitaxially Grown Boron Doped Si by 5.4 MeV α -Particles. Materials Research Society Symposia Proceedings, 1998, 510, 449.	0.1	0
84	Electrical characterization of defects in SiCl ₄ plasma-etched n-GaAs and Pd Schottky diodes fabricated on it. Applied Physics Letters, 1997, 71, 668-670.	3.3	1
85	Electrical and Optical Characterisation of Defects Induced in Epitaxially Grown n-Si During 1 keV Noble Gas Ion Bombardment. Materials Science Forum, 1997, 258-263, 565-570.	0.3	0
86	Electrical Characterization of Defects Introduced During Plasma-Based Processing of GaAs. Materials Science Forum, 1997, 258-263, 1045-1050.	0.3	0
87	Defect Formation by Low Energy Ions during Sputter Deposition of TiW and Au on Epitaxially Grown n-Si at Different Plasma Pressures. Materials Science Forum, 1997, 248-249, 249-252.	0.3	0
88	Electronic properties of defects created in epitaxially grown n-Si by low energy He and Ar ions. Nuclear Instruments & Methods in Physics Research B, 1997, 127-128, 393-396.	1.4	0
89	Electrical Characterization Of Defects Introduced During Plasma-Based Processing Of GaAs. Materials Research Society Symposia Proceedings, 1996, 442, 51.	0.1	1
90	Optical And Electrical Characterisation Study Of SiCl ₄ Reactive Ion Etched GaAs. Materials Research Society Symposia Proceedings, 1996, 442, 75.	0.1	1

#	ARTICLE	IF	CITATIONS
91	Electronic Properties Of Defects Formed In n-Si During Sputter-Etching In An Ar Plasma. Materials Research Society Symposia Proceedings, 1996, 442, 87.	0.1	0
92	Metal contacts to gallium arsenide. Journal of Electronic Materials, 1996, 25, 1695-1702.	2.2	17
93	Electric Field Enhanced Emission from Two Alpha-Particle Irradiation Induced Traps in n-GaAs. Japanese Journal of Applied Physics, 1996, 35, L1-L3.	1.5	8
94	Electronic and annealing properties of a metastable He-ion implantation induced defect in GaAs. Nuclear Instruments & Methods in Physics Research B, 1995, 106, 323-327.	1.4	17
95	New electron irradiation induced electron trap in epitaxially grown Si-doped n-GaAs. Applied Physics Letters, 1995, 67, 3277-3279.	3.3	8
96	Electronic and transformation properties of a metastable defect introduced inn-type GaAs by α -particle irradiation. Physical Review B, 1995, 51, 17521-17525.	3.2	17
97	Electric-field-enhanced emission from radiation-induced hole traps in p-GaAs. Semiconductor Science and Technology, 1995, 10, 1376-1381.	2.0	16
98	Electric Field Effect on the Emission of Electron-Irradiation-Induced Defects in n-GaAs. Japanese Journal of Applied Physics, 1994, 33, 1949-1953.	1.5	9
99	Hole defects in molecular beam epitaxially grown n-GaAs introduced by alpha irradiation. Journal of Applied Physics, 1994, 75, 1222-1224.	2.5	6
100	Fermi level pinning by various metal Schottky contacts on (100) OMVPE-grown n-GaAs. Thin Solid Films, 1994, 249, 95-99.	1.8	4
101	The effect of alpha-particle and proton irradiation on the electrical and defect properties of n-GaAs. Nuclear Instruments & Methods in Physics Research B, 1994, 90, 349-353.	1.4	44
102	Electrical characteristics of neutron irradiation induced defects in n-GaAs. Nuclear Instruments & Methods in Physics Research B, 1994, 90, 387-391.	1.4	18
103	Ruthenium and ruthenium-based contacts to GaAs. Applied Surface Science, 1993, 70-71, 511-514.	6.1	8
104	Electrical characterization of defects introduced in n-GaAs by alpha and beta irradiation from radionuclides. Applied Physics A: Solids and Surfaces, 1993, 56, 547-553.	1.4	45
105	Electrical and defect characterization of n-Type GaAs irradiated with α -particles using a van de graaff accelerator and an Am-241 radio-nuclide source. Physica Status Solidi A, 1993, 140, 381-390.	1.7	8
106	Effect of electron-beam deposition rate on the electrical properties of Ti/ and Pt/n-GaAs contacts. Thin Solid Films, 1993, 235, 163-168.	1.8	1
107	Deep Level Transient Spectroscopy Characterization of Electron Irradiation Induced Hole Traps in p-GaAs Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1993, 32, L974-L977.	1.5	14
108	Electrical characteristics of Ar-ion sputter induced defects in epitaxially grown n-GaAs. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 2366.	1.6	32

#	ARTICLE	IF	CITATIONS
109	Modified sample holder for low-temperature deep-level transient spectroscopy, current-voltage and capacitance-voltage measurements. Review of Scientific Instruments, 1992, 63, 2101-2102.	1.3	3
110	Vacuum annealing characteristics of electron beam evaporated ruthenium contacts to n-GaAs grown by organometallic vapour phase epitaxy. Thin Solid Films, 1992, 213, 113-116.	1.8	7
111	Electrical Characterization of Metastable Defects Introduced in GaN by Eu-Ion Implantation. Materials Science Forum, 0, 679-680, 804-807.	0.3	5